Ikai Lo

List of Publications by Year
in descending order

56 papers	911 citations	516710 16 h-index	477307 29 g-index
57 all docs	57 docs citations	57 times ranked	726 citing authors

#	Article	IF	Citations
1	Influence of lattice misfit on crack formation during the epitaxy of In Al1-N on GaN. Journal of Alloys and Compounds, 2022, 890, 161797.	5.5	3
2	Growth and Characterization of GaN/InxGa1â^'xN/InyAl1â^'yN Quantum Wells by Plasma-Assisted Molecular Beam Epitaxy. Crystals, 2022, 12, 417.	2.2	6
3	Anisotropic Strain on GaN Microdisks Grown by Plasma-Assisted Molecular Beam Epitaxy. Crystals, 2020, 10, 899.	2.2	1
4	Indium-Incorporation with InxGa1-xN Layers on GaN-Microdisks by Plasma-Assisted Molecular Beam Epitaxy. Crystals, 2019, 9, 308.	2.2	4
5	Advances in GaN Crystals and Their Applications. Crystals, 2018, 8, 117.	2.2	7
6	Finite growth of InGaN/GaN triple-quantum-well microdisks on LiAlO2 substrate. AIP Advances, 2018, 8, .	1.3	3
7	GaN and InN Hexagonal Microdisks. , 2018, , .		1
8	Strain of M-plane GaN epitaxial layer grown on Î²-LiGaO2 (100) by plasma-assisted molecular beam epitaxy. AIP Advances, 2018, 8, 075116.	1.3	1
9	Refractive Index Measurement Using the Laser Profiler. Physics Procedia, 2017, 86, 176-180.	1.2	5
10	Evolution of Metallic Conductivity in Epitaxial ZnO Thin Films on Systematic Al Doping. Journal of Electronic Materials, 2017, 46, 2030-2039.	2.2	6
11	Growth and Characterization of M-Plane GaN Thin Films Grown on Î³-LiAlO2 (100) Substrates. Scanning, 2017, 2017, 1-7.	1.5	1
12	Improving Performance by Doping Gadolinium Into the Indium-Tinâ€“Oxide Electrode in HfO₂-Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 584-587.	3.9	28
13	Characterization of M -plane GaN thin films grown on misoriented Î³-LiAlO 2 (100) substrates. Journal of Crystal Growth, 2016, 450, 197-202.	1.5	7
14	Obtaining Lower Forming Voltage and Self-Compliance Current by Using a Nitride Gas/Indiumâ€“Tin Oxide Insulator in Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2016, 63, 4769-4775.	3.0	9
15	Growth of InN hexagonal microdisks. AIP Advances, 2016, 6, 085015.	1.3	6
16	Resistive Switching Mechanism of Oxygen-Rich Indium Tin Oxide Resistance Random Access Memory. IEEE Electron Device Letters, 2016, 37, 408-411.	3.9	31
17	Bulk Oxygenâ€“Ion Storage in Indiumâ€“Tinâ€“Oxide Electrode for Improved Performance of HfO₂-Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 280-283.	3.9	50
18	Epitaxial growth ofM-plane GaN on ZnO micro-rods by plasma-assisted molecular beam epitaxy. AIP Advances, 2015, 5, 127201.	1.3	1

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19	Direct growth of heteroepitaxial CuInSe2 on GaN (0001) by molecular beam epitaxy. Thin Solid Films, 2015, 574, 132-135.	1.8	6
20	Green light emission by InGaN/GaN multiple-quantum-well microdisks. Applied Physics Letters, 2014, 104, .	3.3	10
21	Electrical contact for wurtzite GaN microdisks. Applied Physics Letters, 2014, 105, 082101.	3.3	5
22	The growth of heteroepitaxial CuInSe2 on free-standing N-polar GaN. AIP Advances, 2014, 4, .	1.3	2
23	Growth of wurtzite and zinc-blende phased GaN on silicon (100) substrate with sputtered AlN buffer layer. Journal of Crystal Growth, 2013, 382, 1-6.	1.5	9
24	Characterization of GaN microstructures grown by plasma-assisted molecular beam epitaxy. AIP Advances, 2013, 3, 062134.	1.3	0
25	InGaN/GaN single-quantum-well microdisks. Applied Physics Letters, 2012, 100, .	3.3	12
26	Spin splitting in bulk wurtzite AlN under biaxial strain. Journal of Applied Physics, 2012, 111, 103716.	2.5	0
27	Characterization of -plane GaN thin film grown on pre-annealing Î²-LiGaO2 (100) substrate. Thin Solid Films, 2012, 526, 87-91.	1.8	0
28	Improvement of M-plane GaN thin film grown on pre-annealing Î²-LiGaO2 (100) substrate. Journal of Crystal Growth, 2012, 340, 61-65.	1.5	8
29	Characterization of M-plane GaN film grown on Î²-LiGaO2 (100) by plasma-assisted molecular beam epitaxy. Thin Solid Films, 2011, 519, 3569-3572.	1.8	10
30	Growth of InN thin films on ZnO substrate by plasma-assisted molecular beam epitaxy. Journal of Physics and Chemistry of Solids, 2010, 71, 1664-1668.	4.0	12
31	Self-confined GaN heterophased quantum wells. Applied Physics Letters, 2010, 96, 222105.	3.3	3
32	Influence of positive bias stress on N2O plasma improved InGaZnO thin film transistor. Applied Physics Letters, 2010, 96, .	3.3	158
33	Crystal-Field and Strain Effects on Minimum-Spin-Splitting Surfaces in Bulk Wurtzite Materials. Journal of the Physical Society of Japan, 2010, 79, 093705.	1.6	1
34	Spin-degenerate surface and the resonant spin lifetime transistor in wurtzite structures. Journal of Applied Physics, 2010, 108, 083718.	2.5	10
35	Self-assembled GaN hexagonal micropyramid and microdisk. Applied Physics Letters, 2009, 94, .	3.3	22
36	Spin splitting in AlxGa1â^'xN/GaN quasiballistic quantum wires. Journal of Applied Physics, 2009, 105, 093716.	2.5	8

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37	Giant optical anisotropy in R-plane GaN/AlGaN quantum wells caused by valence band mixing effect. Physics Letters, Section A: General, Atomic and Solid State Physics, 2008, 372, 1691-1694.	2.1	2
38	Self-Assembledc-Plane GaN Nanopillars on Î³-LiAlO2Substrate Grown by Plasma-Assisted Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2008, 47, 891-895.	1.5	16
39	Spin-splitting in an AlxGa1â^'xN/GaN nanowire for a quantum-ring interferometer. Applied Physics Letters, 2008, 93, .	3.3	10
40	Application of block diagonal technique to Hamiltonian matrix in performing spin-splitting calculations for GaAs zincblende bulk and quantum wells. Journal of Applied Physics, 2008, 104, .	2.5	6
41	Line defects of M-plane GaN grown on Î³-LiAlO2 by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2008, 92, .	3.3	18
42	Anomalousk-dependent spin splitting in wurtziteAlxGa1â^'xNâ•GaNheterostructures. Physical Review B, 2007, 75, .	3.2	34
43	Optical anisotropy in [hkil]-oriented wurtzite semiconductor quantum wells. Journal of Applied Physics, 2007, 101, 043104.	2.5	17
44	Dresselhaus effect in bulk wurtzite materials. Applied Physics Letters, 2007, 91, .	3.3	47
45	Effect of bulk inversion asymmetry on optical transitions of zinc blende semiconductor quantum wells. Journal of Applied Physics, 2007, 101, 046105.	2.5	4
46	Gate-controlled spin splitting in GaNâ•AlN quantum wells. Applied Physics Letters, 2006, 88, 082108.	3.3	22
47	Zero-field spin splitting in modulation-doped AlxGa1â^'xNâ•GaN two-dimensional electron systems. Applied Physics Letters, 2005, 86, 222102.	3.3	35
48	Wurtzite structure effects on spin splitting inGaNâ•AlNquantum wells. Physical Review B, 2005, 72, .	3.2	32
49	Exchange-enhanced gâ€factors in an Al0.25Ga0.75Nâ•GaN two-dimensional electron system. Journal of Applied Physics, 2004, 96, 7370-7373.	2.5	32
50	Effect of N to Ga flux ratio on the GaN surface morphologies grown at high temperature by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 2004, 95, 460-465.	2.5	34
51	Improved characteristics of metamorphic InAlAsâ•InGaAs high electron mobility transistor with symmetric graded In[sub x]Ga[sub 1â^'x]As channel. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2429.	1.6	2
52	Spin splitting in modulation-dopedAlxGa1â^'xN/GaNheterostructures. Physical Review B, 2002, 65, .	3.2	89
53	Positive and negative persistent photoconductivities in semimetallic AlxGa1â^'xSb/InAs quantum wells. Journal of Applied Physics, 1999, 86, 3152-3158.	2.5	10
54	Conduction-Valence Landau Level Mixing Effect. Physical Review Letters, 1996, 77, 2053-2056.	7.8	44

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55	Electronic properties ofAlxGa1â^'xSb/InAs quantum wells. Physical Review B, 1994, 50, 5316-5322.	3.2	11
56	A Study of Magnetic-Field-Induced Semimetal to Semiconductor Transition in AlxGai1-xSb/InAs Quantum Wells. Materials Research Society Symposia Proceedings, 1993, 326, 317.	0.1	0